

HCC/HCF4066B

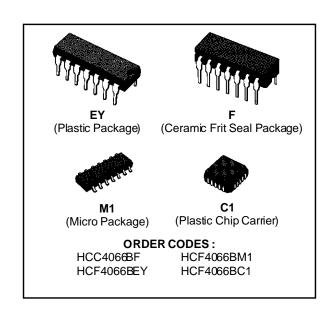
QUAD BILATERAL SWITCH FOR TRANSMISSION OR MULTIPLEXING OF ANALOG OR DIGITAL SIGNALS

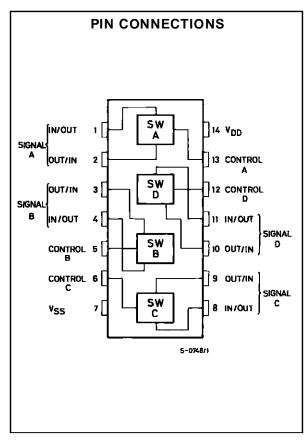
- 15V DIGITAL OR ± 7.5V PEAK-TO-PEAK **SWITCHING**
- 80Ω TYPICAL ON RESISTANCE FOR 15V **OPERATION**
- SWITCH ON RESISTANCE MATCHED TO OVER 15V SIGNAL-INPUT WITHIN 5Ω **RANGE**
- ON RESISTANCE FLAT OVER FULL PEAK-TO-PEAK SIGNAL RANGE
- HIGH ON/OFF OUTPUT-VOLTAGE RATIO: 65dB TYP. @ $f_{is} = 10kHz$, $R_L = 10k\Omega$
- HIGH DEGREE OF LINEARITY: < 0.5% DIS-TORTION TYP. @ $f_{is} = 1kHz$, $V_{is} = 5 Vp-p$, $V_{DD} - V_{SS} \ge 10V$, $R_L = 10k\Omega$
- EXTREMELY LOW OFF SWITCH LEAKAGE RESULTING IN VERY LOW OFFSET CUR-RENT AND HIGH EFFECTIVE OFF RESIST-ANCE: 10pA TYP. @ VDD - VSS = 10V. $T_A = 25^{\circ}C$
- EXTREMELY HIGH CONTROL INPUT IMPED-ANCE (control circuit isolated from signal circuit): $10^{12} \Omega$ TYP.
- LOW CROSSTALK BETWEEN SWITCHES:-50dB TYP. @ $f_{is} = 0.9MHz$, $R_L = 1k\Omega$
- MATCHED CONTROL-INPUT TO SIGNAL-OUTPUT CAPACITANCE: REDUCES OUT-**PUT SIGNAL TRANSIENTS**
- FREQUENCY RESPONSE, SWITCH ON = 40MHz (typ.)
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDECTEN-TATIVE STANDARD Nº. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

DESCRIPTION

FOR HCC DEVICE

The HCC4066B (extended temperature range) and HCF4066B (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage. The HCC/HCF4066B is a quad bilateral switch intended for the transmission or multiplexing of analog or digital signals. It is pin-for-



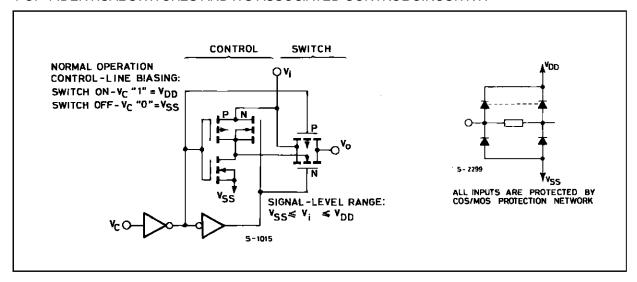


June 1989 1/11 pin compatible with **HCC/HCF4016B**, but exhibits a much lower ON resistance. In addition, the ON resistance is relatively constant over the full input-signal range. The **HCC/HCF4066B** consists of four independent bilateral switches. A single control signal is required per switch. Both the p and the n device in a given switch are biased ON or OFF simultaneously by the control signal. As shown in schematic diagram, the well of the n-channel device on each switch is either tied to the input when the switch is ON or to Vss when the switch is OFF. This

configuration eliminates the variation of the switch-transistor threshold voltage with input signal, and thus keeps the ON resistance low over the full operating-signal range. The advantages over single-channel switches include peak input signal voltage swings equal to the full supply voltage, and more constant ON impedance over the input-signal range. For sample-and-hold applications, however, the **HCC/HCF4016B** is recommended.

SCHEMATIC DIAGRAM

1 OF 4 IDENTICAL SWITCHES AND ITS ASSOCIATED CONTROL CIRCUITRY.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V_{i}	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I_1	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package-temperature Range	200	mW mW
Top	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.



RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_{I}	Input Voltage	0 to V _{DD}	V
Top	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C

ELECTRICAL CHARACTERISTICS

 $(T_{amb} = 25^{\circ}C, typical temperature coefficient for all V_{DD} values is 0,3%/°C)$

			Test Cond	dition	ıs				Value				
Symbol	Parame	ter		Vı	V _{DD}	TL	ow*		25°C		T _H	igh*	Unit
				(V)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
ΙL	Quiescent			0/ 5	5		0.25		0.01	0.25		7.5	
	Device Current (all	HCC		0/10	10		0.5		0.01	0.5		15	
	switches	Types		0/15	15		1		0.01	1		30	
	ON or all switches			0/20	20		5		0.02	5		150	μΑ
	OFF)	HCF		0/ 5	5		1		0.01	1		7.5	
		Types		0/10	10		2		0.01	2		15	
				0/15	15		4		0.01	4		30	
SIGNA	L INPUTS (V _{is}) and	Outputs (V _{os})										
R _{ON}	On	HCC	$R_{\rm L} = 10 \rm kg Ke mm$		5		800		470	1050		1300	
	Resistance	Types			turn	10		310		180	400		550
			to $\frac{V_{DD} - V_{SS}}{2}$		15		200		125	240		320	Ω
		HCF	$V_{is} = V_{SS}$ to V_{I}	DD	5		850		470	1050		1200	22
		Types			10		330		180	400		500	
					15		210		125	240		300	
ΔΟΝ	Resistance	0	R_L 10k Ω , V_C =	V_{DD}	5				15				
	between ar Switches, Δ				10				10				Ω
	,	ON			15				5				
TDH	Total Harmo Distorsion	onic	$\begin{array}{l} V_{C} = V_{DD} = 5V, \\ V_{SS} = -5V, \\ V_{is} \left(p\text{-}p\right) = 5V \\ \text{(sine wave centered in } \\ R_{L} = 10k\Omega, \\ f_{is} = 1\text{kHz sine wave} \end{array}$		•				0.4				%
	- 3 dB Cuto Frequency (on)		$\begin{aligned} &V_{C}=V_{DD}=5V\\ &V_{SS}=-5V,\\ &V_{is}\left(p\text{-}p\right)=5V\\ &(\text{sine wave cen}\\ &0V)\\ &R_{L}=1k\Omega \end{aligned}$		l on				40				MHz



^{*} $T_{Low} = -55^{\circ}\text{C}$ for HCC device : -40°C for HCF device. * $T_{High} = +125^{\circ}\text{C}$ for HCC device : $+85^{\circ}\text{C}$ for HCF device. The Noise Margin for both "1" and "0" level is : 1V min. with $V_{DD} = 5V$, 2V min. with $V_{DD} = 10V$, 2.5V min. with $V_{DD} = 15V$.

ELECTRICAL CHARACTERISTICS (continued)

			Test Conditions					Value				
Symbol	Parame	ter		V _{DD}	T _L	* ow		25°C		T _H	* igh	Unit
				(V)	Min.	Max.	Min.	Тур.	Max.	Min.		
	- 50 dB Feedthroug Frequency(off)		$\begin{aligned} &V_C = V_{SS} = -5V, \\ &V_{is} \left(p\text{-}p \right) = 5V \\ &(\text{sine wave centured} \\ &0V) \\ &R_L = 1k\Omega \end{aligned}$	on				1				MHz
	- 50 dB Cro Frequency	osstalk	$\begin{aligned} &V_{C}\left(A\right) = V_{DD} = + 5V\\ &V_{C}\left(B\right) = V_{SS} = - 5V\\ &V_{is}\left(A\right) = 5Vp-p,\\ &50\Omega \text{ source}\\ &R_{L} = 1 k\Omega \end{aligned}$					8				MHz
t _{pd}	(signal inpu	ut to	$R_L = 200k\Omega$ $V_C = V_{DD}, V_{SS} = GNI$		5			20	40			
	signal outpu	ut)	$C_L = 50 pF$, $V_{is} = 10^{\circ}$ (square wave centure 5V)		10			10	20			ns
			t _r , t _f = 20ns		15			7	15			
C _{is}	Input Capad	citance	$V_{DD} = + 5V$ $V_{C} = V_{SS} = -5V$					8				
C _{os}	Output Capacitance	е						8				pF
C _{ios}	Feedthroug	h						0.5				
	Input/Output Leakage Current Switch OFF	HCC Types	$ \begin{aligned} &V_{C} = 0V \\ &V_{is} = 18V \; ; \; V_{os} \\ &= 0V \\ &V_{is} = 0V \; ; \; V_{os} \\ &= 18V \end{aligned} $	18		± 0.1		±10 ⁻³	± 0.1		± 1	μΑ
		HCF Types	$V_{C} = 0V$ $V_{is} = 15V$; V_{os} $= 0V$ $V_{is} = 0V$; V_{os} $= 15V$	15		± 0.3		±10 ⁻³	± 0.3		± 1	
CONTR	OL (V _C)											
V _{ILC}		ut Low	I _{is} < 10μΑ	5		1			1		1	
	Voltage		$V_{is} = V_{SS}, V_{os} = V_{DD}$ and	10		2			2		2	V
			$V_{is} = V_{DD}, V_{os} = V_{SS}$	15		2			2		2	
V _{IHC}	Control Input High			5	3.5		3.5			3.5		
	Voltage			10	7		7			7		V
				15	11		11			11		
I _{II+} , I _{IL}	Input Leakage	HCC Types		18		± 0.1		±10 ⁻⁵	± 0.1		± 1	μΑ
	Current		$V_{DD} - V_{SS} = 15V$ $V_{CC} \le V_{DD} - V_{SS}$	15		± 0.3		±10 ⁻⁵	± 0.3		± 1	μΛ

* $T_{Low} = -55^{\circ}\text{C}$ for HCC device : -40°C for HCF device. * $T_{High} = +125^{\circ}\text{C}$ for HCC device : $+85^{\circ}\text{C}$ for HCF device. The Noise Margin for both "1" and "0" level is : 1V min. with $V_{DD} = 5V$, 2V min. with $V_{DD} = 10V$, 2.5V min. with $V_{DD} = 15V$.

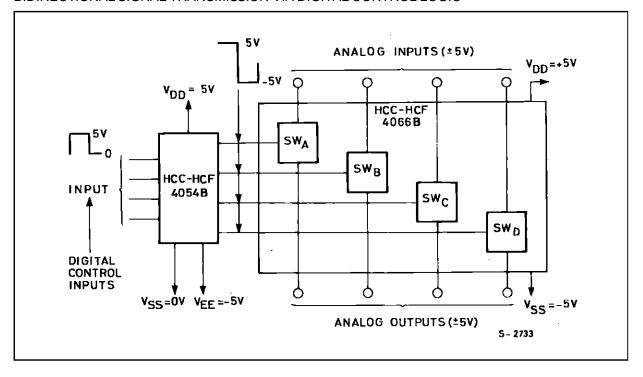


ELECTRICAL CHARACTERISTICS (continued)

		Test Conditions	Test Conditions			Value					
Symbol	Parameter	V _{DD}		T _{Low} *			25°C		T _H	igh*	Unit
			(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
	Crosstalk (control input to signal output)	$V_C = 10V$ (sq. wave) t_r , $t_f = 20$ ns $R_L = 10k\Omega$	10				50				mV
		$V_{IN} = V_{DD}$	5				35	70			
	Propagation Delay		10				20	40			ns
		$C_L = 50pF$ $R_L = 1k\Omega$	15				15	30			
		$\begin{aligned} &V_{is} = V_{DD}, &V_{SS} = GND \\ &R_L = 1 k\Omega \text{ to gnd} \\ &C_L = 50 pF \end{aligned}$	5				6				
		$V_C = 10V$ (square wave centured on 5V)	10				9				MHz
		t_r , $t_f = 20$ ns $V_{os} = 1/2V_{os}$ @ 1kHz	15				9.5				
C _I	Input Capacitance	Any Input					5	7.5			pF

TYPICAL APPLICATIONS

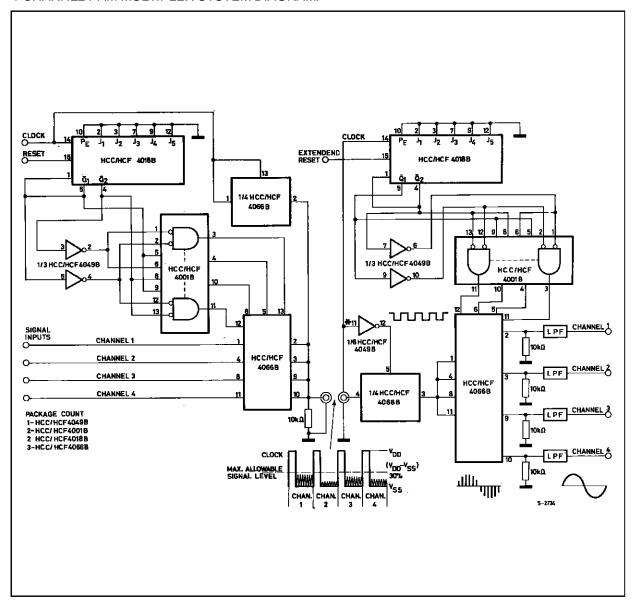
BIDIRECTIONAL SIGNAL TRANSMISSION VIA DIGITAL CONTROL LOGIC



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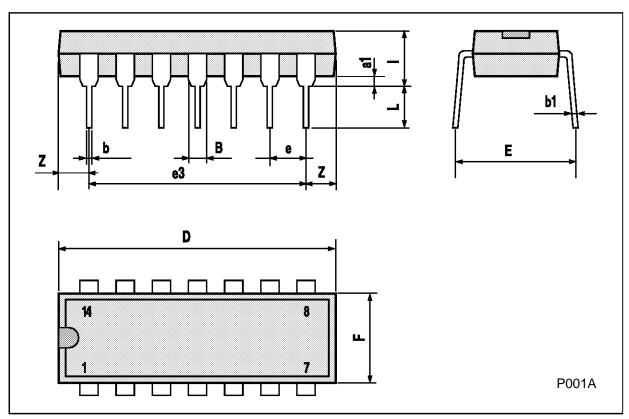
TYPICAL APPLICATIONS (continued)

4-CHANNEL PAM MULTIPLEX SYSTEM DIAGRAM.



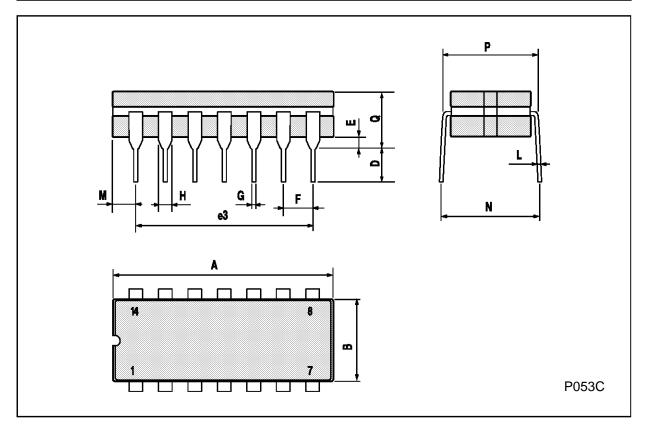
Plastic DIP14 MECHANICAL DATA

DIM.		mm				
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



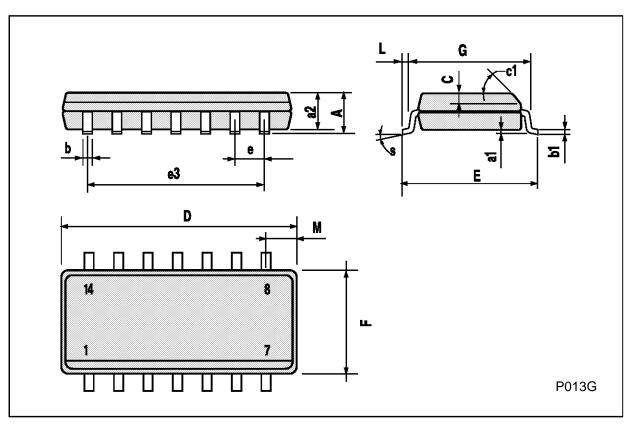
Ceramic DIP14/1 MECHANICAL DATA

DIM.		mm			inch	
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			20			0.787
В			7.0			0.276
D		3.3			0.130	
Е	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
М	1.52		2.54	0.060		0.100
N			10.3			0.406
Р	7.8		8.05	0.307		0.317
Q			5.08			0.200



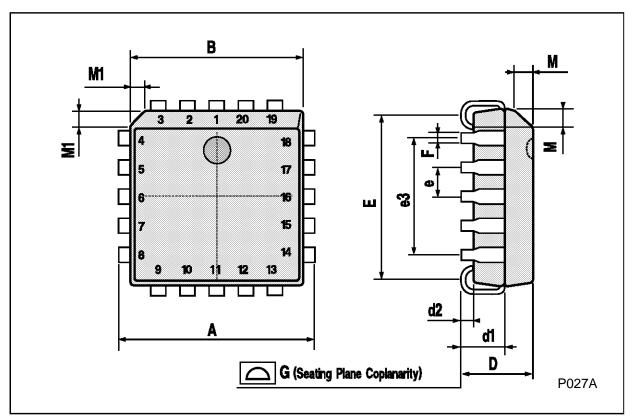
SO14 MECHANICAL DATA

DIM.		mm		inch				
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)				
D	8.55		8.75	0.336		0.344		
E	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		7.62			0.300			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.68			0.026		
S			8° (ı	max.)				



PLCC20 MECHANICAL DATA

DIM.		mm				
Dini.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	9.78		10.03	0.385		0.395
В	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
е		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
М		1.27			0.050	
M1		1.14			0.045	



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